NSN 5962-01-421-1162

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View Online at https://aerobasegroup.com/nsn/5962-01-421-1162

Body Length:

Between 0.442 inches and 0.460 inches

Body Width:

Between 0.442 inches and 0.460 inches

Body Height:

Between 0.060 inches and 0.100 inches

Maximum Power Dissipation Rating:

1.04 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Pacer dawn

Features Provided:

Bipolar and burn in, mil-std-883, class b and electrostatic sensitive and monolithic and programmed and tested to mil-std-883

Inclosure Material:

Ceramic

Inclosure Configuration:

Leadless flat pack

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

14 input

Criticality Code Justification:

Cbbl

Case Outline Source And Designator:

C-4 mil-m-38510

Current Rating Per Characteristic:

190.00 milliamperes reverse current, dc absolute

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, programmed (prom 93z665a)

Voltage Rating And Type Per Characteristic:

-0.3 volts power source and 7.0 volts power source and 5.5 volts input

Capitance Rating Per Characteristic:

10.00 input picofarads and 15.00 output picofarads

Time Rating Per Chacteristic:

100.00 nanoseconds propagation delay and 100.00 nanoseconds access

Memory Device Type:

Prom

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Special Features:

Altered item programmed using 14933 82009023a (which is 81349 m38510/217816354pg68

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

28 leadless

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

A458a0